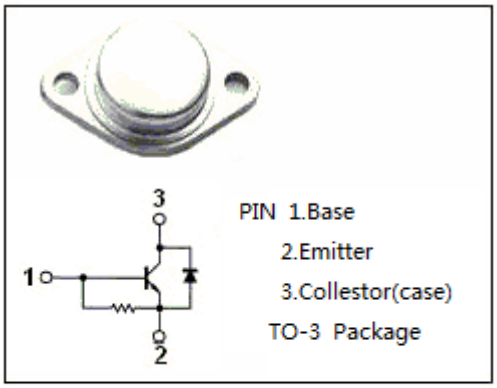
isc Silicon NPN Power Transistor 2SD956

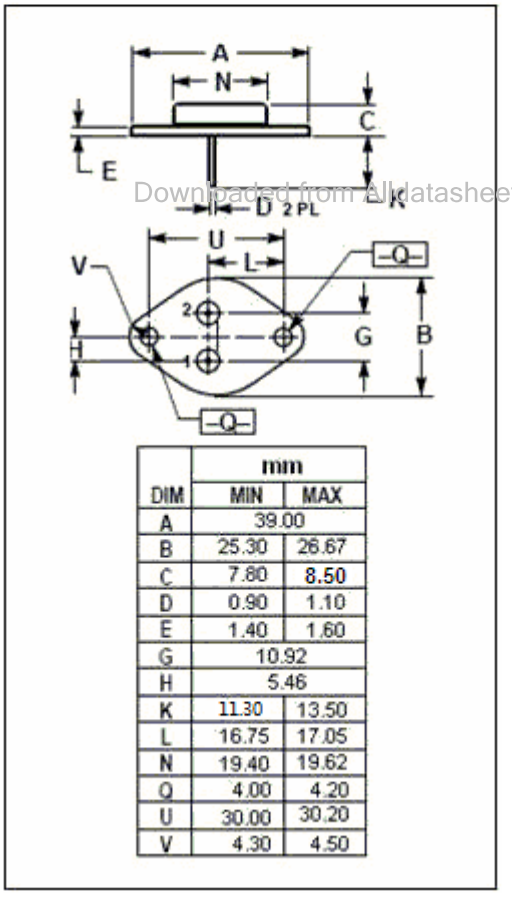
DESCRIPTION

- High Breakdown Voltage-
  : V_{CBO}= 1500V (Min)
- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= 4.0V(Max.)@ I_C= 2A
- Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for line-operated horizontal deflection output applications.



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CES}	Collector-Emitter Voltage	1500	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current- Continuous	2.5	A
I_{CP}	Collector Current- Peak	4.5	A
P_C	Collector Power Dissipation @ T_C= 25℃	50	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

isc Silicon NPN Power Transistor 2SD956

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{EBO}	Emitter-Base Breakdown Voltage	I_E= 200mA; I_C= 0	5.0			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B= 0.75A			4.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 2A; I_B= 0.75A			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 750V; I_E= 0			50	μA
		V_{CB}= 1500V; I_E= 0			0.5	mA
h_{FE}	DC Current Gain	I_C= 1A; V_{CE}= 5V	8		36	
V_{ECF}	C-E Diode Forward Voltage	I_F= 3A			1.7	V
t_{stg}	Storage Time	I_C= 2A, I_{Bend}= 0.75A; L_B= 10μH			10	μs
t_f	Fall Time				1.0	μs

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